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Filing Date		2005-09-22		
First Named Inventor	MEUN	NIER-BEILLARD, PHILIPPE		
Art Unit		2823		
Examiner Name	NGUY	NGUYEN, KHIEM D		
Attorney Docket Number		NL03 0357 US1		

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	1	5378651	А			AGNELLO, PA	UL D.; ET AL			
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	1	AGNELLO, P.D., ET AL; "HEAVY ARSENIC DOPING OF SILICON GROWN BY ATMOSPHERIC-PRESSURE CHEMICAL VAPOR DEPOSITION AT LOW TEMPERATURES"; APPL. PHYS. LETT. 60 (4); JANUARY 27, 1992; PAGES 454 - 456						
	2	AGNELLO, P. D., ET AL; "SILICON EPITAXY FROM SILANE BY ATMOSPHERIC-PRESSURE CHEMICAL VAPOR DEPOSITION AT LOW TEMPERATURES", APPL. PHYS. LETT. 61 (11); SEPTEMBER 14, 1992; PAGES 1298 - 1300						
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